



DUAL P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
001/	50mΩ @V _{GS} = -4.5V	-4.5A
-20V	100mΩ @V _{GS} = -2.5V	-3.2A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotive-products/.

 This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

https://www.diodes.com/quality/product-definitions/

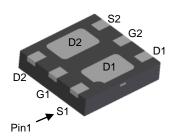
Description and Applications

This MOSFET has been designed to minimize the on-state resistance (RDS(ON)) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Battery Charging
- Power Management Functions
- DC-DC Converters
- Portable Power Adaptors

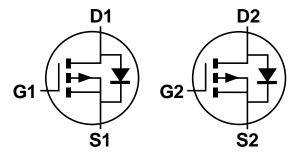
Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208@4
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)



U-DFN2020-6 (Type B)

Bottom View



Internal Schematic

Ordering Information (Note 4)

	1	
Part Number	Case	Packaging
DMP2065UFDB-7	U-DFN2020-6 (Type B)	3,000/Tape & Reel
DMP2065UFDB-13	U-DFN2020-6 (Type B)	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information

Site 1



P5 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Year	2016		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	D		Н		J	K	L	М	N	0	Р	R
Month	lan	Fah	Mar	Δnr	May	lun	lul	Διια	San	Oct	Nov	Dec
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Site 2



P5 = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020) W = Week (ex: a = Week 27; z Represents Week 52 and 53) X = Internal Code (ex: U = Monday)

Date Code Key

Year	2016	•••	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	
Code	6		0	1	2	3	4	5	6	7	8	9	
Week 1-26				27	-52		53						
Code		A-Z			A-Z a-z							Z	
Internal Code	Sun	Sun Mon			Tue	W	ed	Thu		Fri		Sat	
Code	Т		U		V	V	V	Х		Υ		Z	



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	VDSS	-20	V	
Gate-Source Voltage	V _{GSS}	±12	V	
Continuous Drain Current (Note 6) VGS = -4.5V	lo	-4.5 -3.6	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	-25	Α
Maximum Continuous Body Diode Forward Current (No	Is	-1.4	Α	
Avalanche Current (Note 7) L = 0.1mH	las	-13	Α	
Avalanche Energy (Note 7) L = 0.1mH		Eas	9	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T _A = +25°C	PD	0.74	W	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	RеJA	171	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	КөЈА	131	C/VV	
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	1.54	W	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Davi	82		
Thermal Resistance, Junction to Ambient (Note o)	t<10s	Reja	60	°C/W	
Thermal Resistance, Junction to Case (Note 6)	Rejc	13			
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C		

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	IDSS	-	_	-1.0	μA	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	Igss	-	_	±100	nA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-0.4		-1.0	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$
			40	50		$V_{GS} = -4.5V, I_{D} = -2.0A$
Static Drain-Source On-Resistance	Descous	_	55	100	mΩ	$V_{GS} = -2.5V, I_{D} = -2.0A$
Static Diani-Source Off-Resistance	RDS(ON)		75	150	11122	$V_{GS} = -1.8V, I_{D} = -1.6A$
			95	200		$V_{GS} = -1.5V, I_{D} = -1.0A$
Diode Forward Voltage	VsD	1	-0.75	-1.1	V	$V_{GS} = 0V$, $I_{S} = -1A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	Ciss	1	752	_	pF	V 45V V 6V
Output Capacitance	Coss	-	87	_	pF	V _{DS} = -15V, V _{GS} = 0V -f = 1.0MHz
Reverse Transfer Capacitance	Crss	-	78	_	pF	1 = 1.01/1112
Gate Resistance	Rg	-	15.2	_	Ω	$V_{GS} = 0V$, $V_{DS} = 0V$, $f = 1.0MHz$
Total Gate Charge	Qg	1	9.1	_	nC	V 45V V 4V
Gate-Source Charge	Qgs	1	1.2	_	nC	$V_{GS} = -4.5V, V_{DS} = -4V,$
Gate-Drain Charge	Qgd	_	1.9	_	nC	I _D = -3.5A
Turn-On Delay Time	tD(ON)	_	5.4	_	ns	
Turn-On Rise Time	t _R	_	8.3	_	ns	$V_{DS} = -4V$, $V_{GS} = -4.5V$,
Turn-Off Delay Time	t _{D(OFF)}	_	47	_	ns	$R_G = 6\Omega$, $I_D = -1A$
Turn-Off Fall Time	tF	_	20	_	ns]

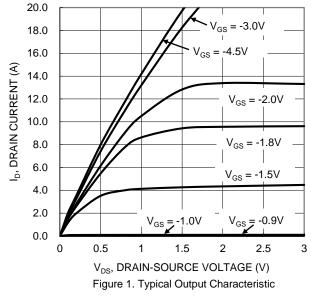
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

^{6.} Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

^{7.} I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.

^{8.} Short duration pulse test used to minimize self-heating effect. 9. Guaranteed by design. Not subject to product testing.





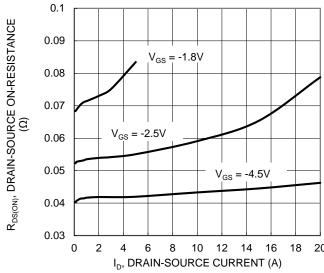


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

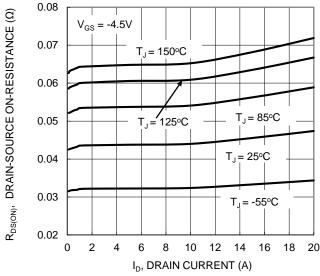


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

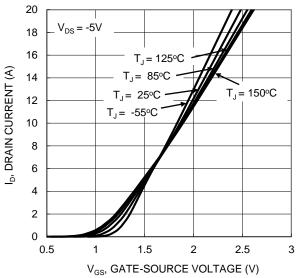
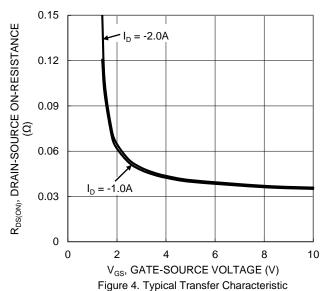
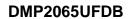


Figure 2. Typical Transfer Characteristic



1.6 R_{DS(ON)}, DRAIN-SOURCE ON-RESISTANCE (NORMALIZED) $V_{GS} = -4.5V, I_{D} = -2.0A$ 1.4 1.2 1 $V_{GS} = -2.5V, I_{D} = -2.0A$ 8.0 0.6 -25 -50 0 25 50 75 100 125 150 T_J, JUNCTION TEMPERATURE (°C)

Figure 6. On-Resistance Variation with Junction Temperature





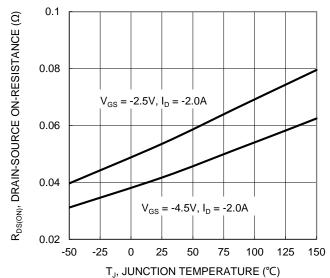


Figure 7. On-Resistance Variation with Junction Temperature

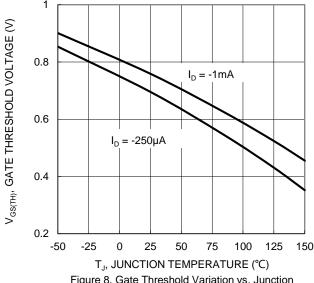
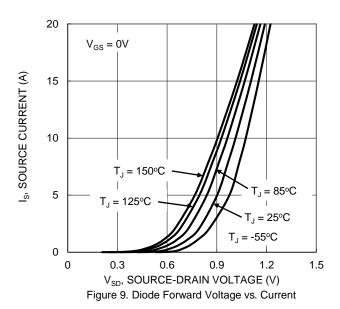
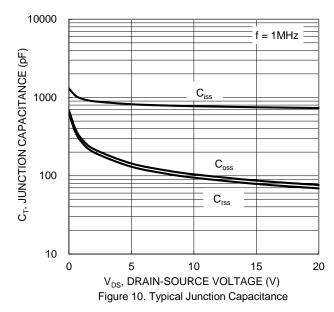


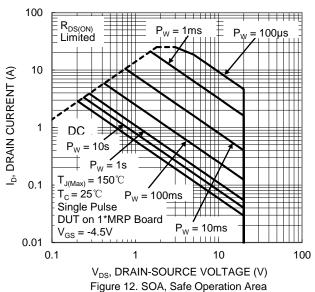
Figure 8. Gate Threshold Variation vs. Junction Temperature



8 6 4 $V_{DS} = -4V, I_{D} = -3.5A$ 2 0 2 4 6 8 10 12 14 16 18 Q_g (nC)

Figure 11. Gate Charge







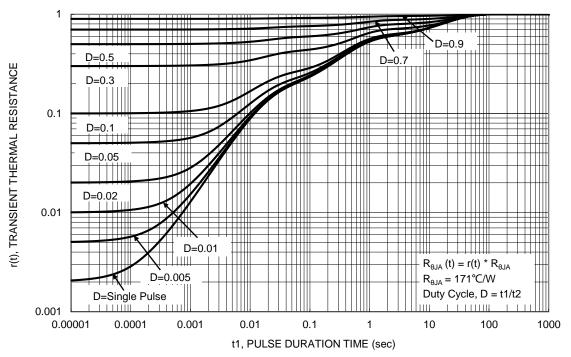


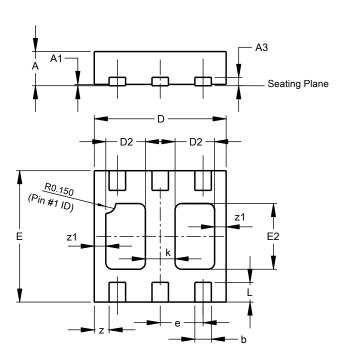
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)

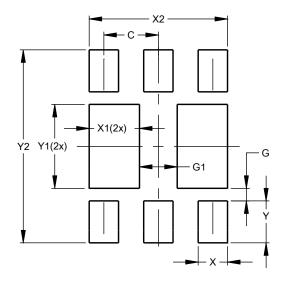


	U-DFN2020-6						
	Тур	е В					
Dim	Min	Max	Тур				
Α	0.545	0.605	0.575				
A1	0.00	0.05	0.02				
A3	-	-	0.13				
b	0.20	0.30	0.25				
D	1.95	2.075	2.00				
D2	0.50	0.70	0.60				
e	-	-	0.65				
Е	1.95	2.075	2.00				
E2	0.90	1.10	1.00				
k	-	-	0.45				
L	0.25	0.35	0.30				
Z	-	-	0.225				
z1	-	-	0.175				
All	Dimens	ions in	mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)



Dimensions	Value
2	(in mm)
C	0.650
G	0.150
G1	0.450
X	0.350
X1	0.600
X2	1.650
Y	0.500
Y1	1.000
Y2	2.300



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